

AMENDMENTS TO THE SPECIFICATION

Please replace the title beginning on page 1, line 5 with the following amended title:

Technical Field of the Invention

Please replace the paragraph beginning on page 1, line 7 with the following amended paragraph:

~~The present invention relates to a~~ A method for fabricating a semiconductor device is disclosed; and more particularly, to a method for fabricating a capacitor by using an atomic layer deposition (ALD) technique is disclosed.

Please replace the title beginning on page 1, line 12 with the following amended title:

Description of the Prior Related Art

Please replace the title beginning on page 6, line 23 with the following amended title:

Summary of the Invention Disclosure

Please replace the paragraph beginning on page 6, line 25 with the following amended paragraph:

~~It is, therefore, an object of the present invention to provide a~~ A method for fabricating a capacitor is disclosed that employs employing ALD-TiN as an upper electrode which is effective and being suitable for preventing a deterioration of a the leakage current property.

Please replace the paragraph beginning on page 7, line 2 with the following amended paragraph:

~~In accordance with an aspect of the present invention, there is provided a~~ A disclosed method for fabricating a capacitor, including the steps of forming a lower electrode on a semiconductor substrate; forming a dielectric layer on the lower electrode; loading the semiconductor substrate containing the dielectric layer into a deposition chamber; nitriding a surface of the dielectric layer while NH₃ gas is flowed into the deposition chamber; and

forming an upper layer by using a source gas NH₃, containing Titanium (Ti) on the nitrated surface of the dielectric layer through an atomic layer deposition (ALD) method.

Please replace the paragraph beginning on page 7, line 16 with the following amended paragraph:

Other ~~objects and aspects and features of the invention disclosed methods~~ will become apparent from the following description of the preferred embodiments with reference to the accompanying drawings, in which wherein:

Please replace the paragraph beginning on page 9, line 24 with the following amended paragraph:

Hereinafter, ~~there is suggested~~ a method for improving a poor leakage current property of a capacitor having an ALD-TiN layer is disclosed and compared to another capacitor having a CVD-TiN layer.

Please replace the paragraph beginning on page 10, line 1 with the following amended paragraph:

Fig. 5 is a flowchart illustrating each step of a method for fabricating a capacitor according to a first preferred embodiment ~~of the present invention~~.

Please replace the paragraph beginning on page 11, line 16 with the following amended paragraph:

Fig. 7 illustrates a flowchart for describing a capacitor fabrication method in accordance with a second preferred embodiment ~~of the present invention~~.

Please replace the paragraph beginning on page 13, line 7 with the following amended paragraph:

Fig. 9 illustrates a flowchart for describing a capacitor fabrication method in accordance with a third embodiment ~~of the present invention~~.